

## NOT RECOMMENDED FOR NEW DESIGN **USE DMN61D9UDW**

DMN5L06DWK

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	$V_{DSS}$	50	V
Gate-Source Voltage	$V_{GSS}$	±20	V
Drain Current Continuous Pulsed (Note 6)	I <sub>D</sub>	305 800	mA

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_D$	250	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	500	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150	°C

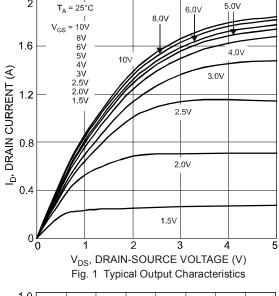
## Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

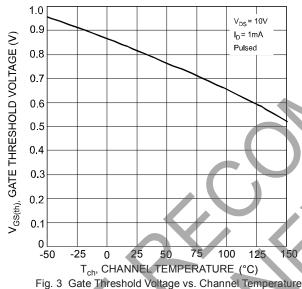
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	-						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	50	· —		V	$V_{GS} = 0V, I_D = 10\mu A$	
Zero Gate Voltage Drain Current @ T <sub>C</sub> = +25°C	1 <sub>DSS</sub>	7		60	nΑ	$V_{DS}$ = 50V, $V_{GS}$ = 0V	
				<u> </u>	μΑ	$V_{GS} = \pm 12V, V_{DS} = 0V$	
Gate-Body Leakage	Igss	_		500	nΑ	$V_{GS} = \pm 10V, V_{DS} = 0V$	
			X	50	nA	$V_{GS} = \pm 5V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.49		1.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
		_		3.0		$V_{GS}$ = 1.8V, $I_{D}$ = 50mA	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_		2.5	Ω	$V_{GS} = 2.5V, I_D = 50mA$	
			_	2.0		$V_{GS} = 5.0V, I_D = 50mA$	
On-State Drain Current	ID(ON)	0.5	1.4	_	Α	$V_{GS} = 10V, V_{DS} = 7.5V$	
Forward Transconductance	Y <sub>FS</sub>	200	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$	
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	0.5	_	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>		_	50	pF	V - 25V V - 0V	
Output Capacitance	Coss		_	25	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	_	5.0	рF	11 - 1.0WHZ	
Gate Resistance	R <sub>G</sub>	_	65		Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	$Q_G$	_	0.4	_	nC	V 45V V 40V	
Gate-Source Charge	Q <sub>GS</sub>	_	0.1	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$	
Gate-Drain Charge	$Q_{GD}$	_	0.1	_	nC	$I_D = 0.25A$	
Turn-On Delay Time	t <sub>D(ON)</sub>		2.1	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	1.8		ns	$V_{DD} = 30V, V_{GS} = 10V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>		14.4	_	ns	$R_G = 25\Omega$ , $I_D = 0.2A$	
Turn-Off Fall Time	$t_{F}$		8.4	_	ns		

Notes:

- Device mounted on FR-4 PCB.
  Pulse width ≤10μS, Duty Cycle ≤1%.
  Short duration pulse test used to minimize self-heating effect.
  Guaranteed by design. Not subject to product testing.







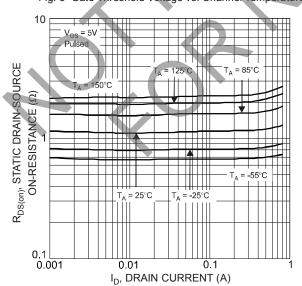
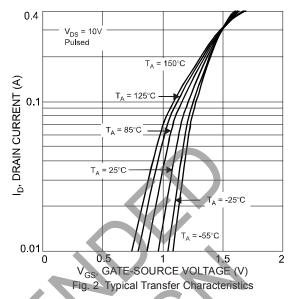


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current



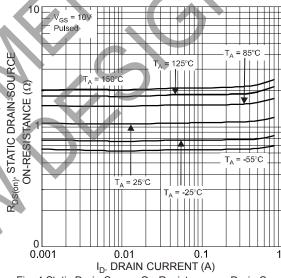


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

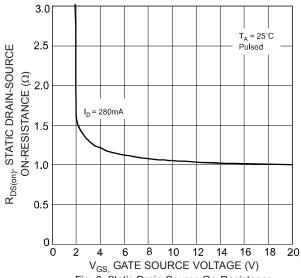


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage



## DMN5L06DWK



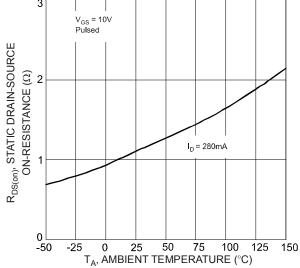


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

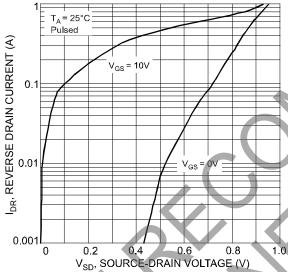
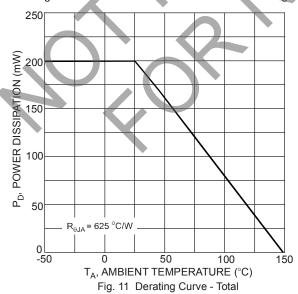


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage



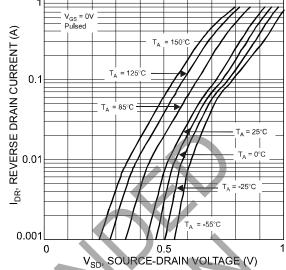


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

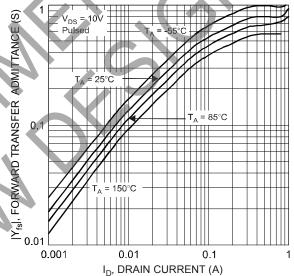


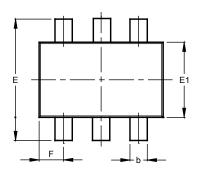
Fig. 10 Forward Transfer Admittance vs. Drain Current

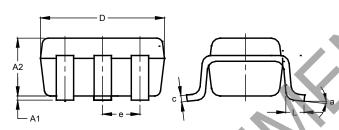


## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT363**



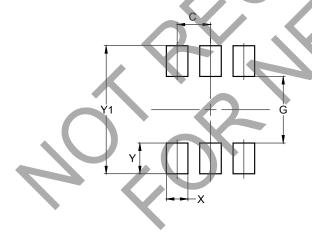


SOT363					
Dim	Min	Max	Тур		
A1	0.00	0.10	0.05		
A2	0.90	1.00	0.95		
b	0.10	0.30	0.25		
C	0.10	0.22	0.11		
D	1.80	2.20	2.15		
Ш	2.00	2.20	2.10		
E1	1.15	1.35	1.30		
е	0.650 BSC				
F	0.40	0.45	0.425		
4	0.25	0.40	0.30		
а	°	8°			
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### **SOT363**



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Υ	0.600
Y1	2.500



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DMN5L06DWK

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